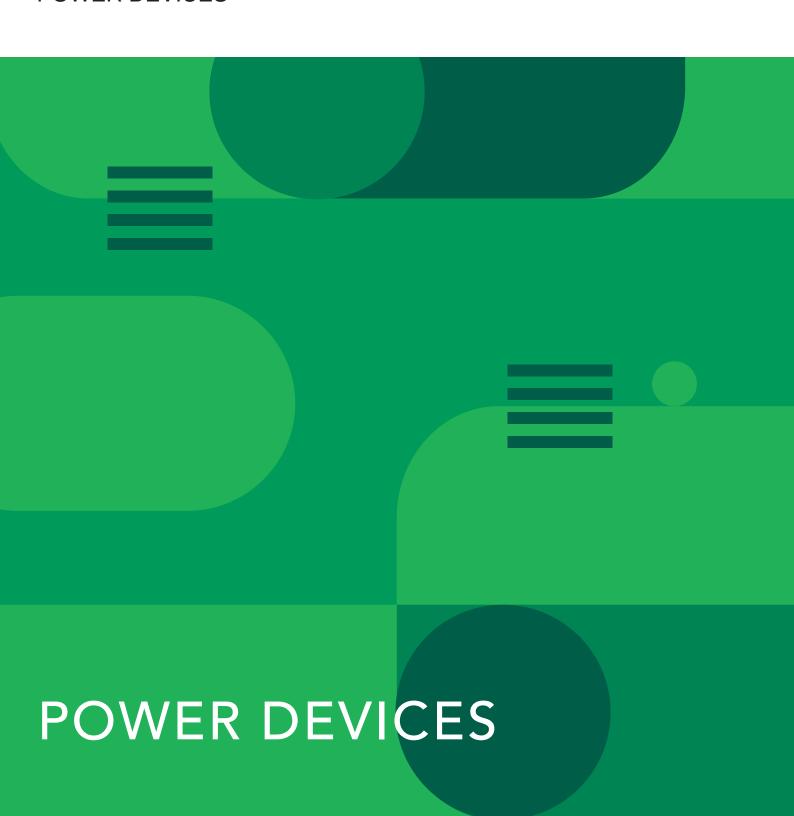
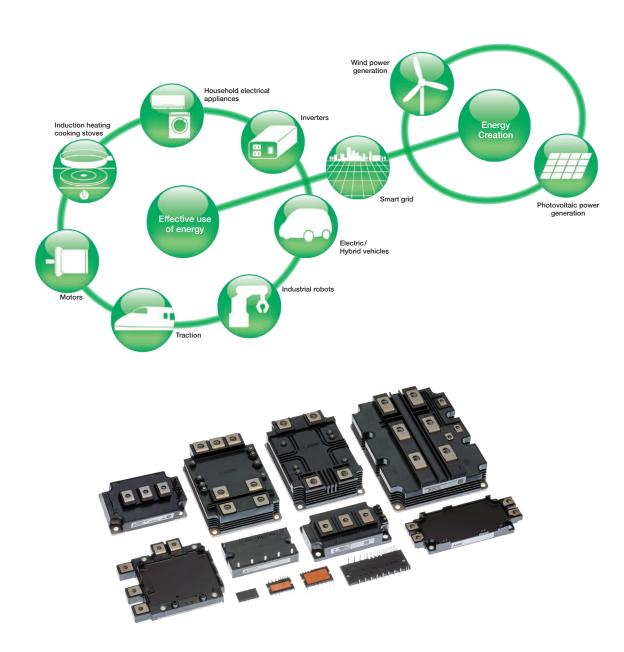


POWER DEVICES



Innovative Power Devices for a Sustainable Future

Mitsubishi Electric power modules are at the forefront of the latest energy innovations that seek to solve global environmental issues while creating a more affluent and comfortable society for all. Some of these innovations are photovoltaic (PV) and wind power generation from renewable energy sources, smart grids realizing efficient supply of power, hybrid/electric vehicles (HVs/EVs) that take the next step in reducing carbon emissions and fuel consumption, and home appliances that achieve ground-breaking energy savings. Whether in appliances, railcars, EVs or industrial systems, our power modules are key elements in changing the way energy is used.



Index

Dundunt	Page			Conne	ection			Rated	Rated	Main Application				
Product	Page	IGBT Module	Intelligent Power Module	MOSFET Module	Diode Module	Discrete Diode	Discrete MOSFET	voltage	current	Main Application				
								600V	15A-30A					
SiC	5-11	. /	. /	. /	. /			1200V	75A-1200A					
Power Modules	J-11	(Hybrid)	V	V	V			1700V	300A,1200A	Home Appliance Industrial equipment				
								3300V	185A-750A	Traction				
SOPIPM	12		✓					600V	2A	Home Appliance				
DIPIPM	12-17		./					600V	5A-75A					
DII II IVI	12-17		V					1200V	5A-100A	Home Appliance				
								600V	75A					
IPM	18-21		$ $ \checkmark					650V	50A-450A					
								1200V	25A-450A	Industrial equipment				
								600V	200A-600A					
								650V	50A-600A					
IGBT Modules	22-31	22-31	/						1200V	35A-1400A				
Wioddies								1700V	75A-1200A	Industrial equipment				
								2000V	200A-1200A					
								1700V	600A-2400A					
HVIGBT	32-34							3300V	400A-1800A					
Modules	32-34	•						4500V	450A-1500A	Traction High Power				
								6500V	600A-1000A					
1 1 /DIODE								3300V	600A-1200A					
HVDIODE Modules	35-36				 			4500V	450A-1500A					
								6500V	300A-1000A	Traction High Power				
MOOFFT								75V						
MOSFET Modules	37				37							100V	100A-300A	
								150V		Industrial equipment				
Power Modules for xEV*1	38-39	✓						650V	300A-700A	xEV				

^{*1} EV: Electric Vehicle

 $^{^{*}}$ 2 SOPIPM, DIPIPM, SLIMDIP, DIPIPM+, DIPPFC and CSTBT are trademarks of Mitsubishi Electric

Development of Mitsubishi Electric SiC Power Devices and Power Electronics Equipment Incorporating Them

Mitsubishi Electric began developing SiC as a new material in the early 1990s. Pursuing special characteristics, we succeeded in developing various elemental technologies.

In 2010, we commercialized the first air conditioner in the world equipped with a SiC power device.

Furthermore, substantial energy-saving effects have been achieved for traction and FA machinery.

We will continue to provide competitive SiC power modules with advanced development and achievements from now on.



Developed large-capacity power module equipped with SiC diode



October 2010 Launched "Kirigamine" inverter air conditioner



2011

January 2011 Verified highest power conversion efficiency*1 for solar power generation system power conditioner (domestic industry)*2

October 2011 Commercialized SiC inverter for use in railcars



2014

February 2014 Developed EV motor drive system with built-in SiC inverter



May 2014
Began shipping
samples of hybrid
SiC power modules
for high-frequency
switching applications



November 2014 Launched Large Hybrid SiC DIPIPM™ for PV Applications



Early 1990s

Developed new material, silicon-carbide (SiC) power semiconductor, maintaining a lead over other companies

2000s

Developed various elemental technologies

2006

January 2006 Successfully developed SiC inverter for driving motor rated at 3.7kW

2009

February 2009 Verified 11kW SiC inverter, world's highest value*1 with approx. 70% reduction in power loss



November 2009 Verified 20kW SiC inverter, world's highest value*1 with approx. 90% reduction in power loss



2012

March 2012 Developed motor system with built-in SiC inverter



September 2012 Verified built-in main circuit system for railcars



July 2012 Began shipping samples of hybrid SiC



December 2012 Launched CNC drive unit equipped with SiC power module



2013

February 2013 Developed SiC for application in elevator control systems

March 2013
Delivered auxiliary power supply systems for railcars



Development of these modules and applications has been partially supported by Japan's Ministry of Economy, Trade and Industry (METI) and New Energy and Industrial Technology Development Organization (NEDO).

2017

March 2017 Launched SiC-SBD



March 2017 Develops World's smallest SiC Inverter for HEVs.



December 2017 Mitsubishi Electric and the University of Tokyo Quantify Factors for Reducing SiC Power Semiconductor Resistance by Two-Thirds

2018

January 2018 New 6.5kV Full-SiC Power Semiconductor Module Achieves World's Highest Power Density

December 2018 Mitsubishi Electric and the University of Tokyo Reveal New Mechanism for Enhancing Reliability of SiC Power Semiconductor Devices

Contributing to the realization of a low-carbon society and more affluent lifestyles



2021

January 2021 Launched Second-generation Full-SiC **Power Modules**



2020

November 2020 Launched 4-terminal SiC-MOSFETs

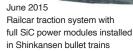


July 2020 Launched SiC-MOSFET

July 2020 **Develops Accurate Circuit** Simulation Technology for SiC-MOSFETs



January 2015 Launched power conditioner for PV equipped with full SiC-IPM*2



2019

June 2019 **Began shipping** samples of 1200V SiC-SBD

February 2019 **Develops Super Compact Power** Unit for Hybrid Electric Vehicle

September 2019 Trench-type SiC-MOSFET with unique electric-field-limiting structure developed



May 2013

modules

Launched SiC power

February 2013 Developed technologies to increase capacities of SiC power modules



December 2013 Launched railcar traction inverter with full SiC power module



2016

April 2016 Launched Super mini Full SiC DIPIPM



October 2016 Launched package air conditioners with full SiC DIPIPM in Japan





May 2016 Launched room air conditioners with full SiC DIPIPM in Japan





^{*1} Researched in press releases by Mitsubishi Electric.

^{*2} Mitsubishi Electric solar-power generation system discontinued on March 31, 2020.

SiC Power Modules

Data sheet here



■ Lineup of SiC Power Modules

Application	Product name	Model	Rating		Connection	States	Page
Арріїодії	1 Toddot Hame	Widdel	Voltages[V]	Current[A]	O I II GOLIO I	Olales	1 456
		FMF300BXZ-24B		300			
		FMF400BX-24B		400	4in1		
		FMF400BXZ-24B		400			6
		RMF400DU-24B		400	2in1(Diode)		
		FMF400DY-24B	1200	400			
	Full SiC Power Modules	FMF600DXZ-24B		600		Commercially available	
		FMF800DX-24B		800	2in1		
		FMF800DXZ-24B		800	2in1		
		FMF1200DXZ-24B	Ī	1200			
Industrial equipment		FMF300DXZ-34B	4700	300			
oquipmont		FMF300E3XZ-34B	1700	300	2in1(Chopper)		
	E 11 0:0 IDM	PMF75CGA120	1000	75	0:.4	Under	
	Full SiC-IPM	PMF75CGAL120	1200	75	6in1	development	
		CMH100DY-24NFH		100	2in1		7
		CMH150DY-24NFH		150			
	Hybrid SiC Power Modules for High-frequency Switching Applications	CMH200DU-24NFH		200			
		CMH300DU-24NFH	1200	300			
		CMH400DU-24NFH	-	400			
		CMH600DU-24NFH		600			
		CMH400HC6-24NFM		400	1in1		
		FMF185DC-66A		185		Commercially available	
	5 # 0'0 B Mad I	FMF375DC-66A	0000	375	-		
raction inverter	Full SiC Power Modules	FMF750DC-66A	3300	750	0:4		8
HVDC system		FMF750DC-66A-1		750	2in1		
	H 144 020 Pr - 14 14	CMH600DC-66X	3300	600			
	Hybrid SiC Power Modules	CMH1200DC-34S	1700	1200			
	5 10:00	PSF15S92F6-A6	05.5	15	0		
Home	Ful SiC Super mini DIPIPM	PSF25S92F6-A6	600	25	6in1		9
appliances .	Ful SiC Super mini DIPPFC	PSF30L92A6-A	600	30	2 Phase interleaved PFC		



Full-SiC Power Modules for Industrial Equipment

Commercially available

Contributes to reducing size/weight of industrial-use inverters

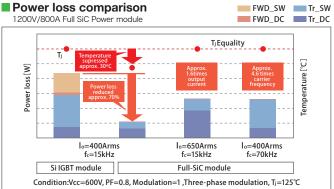
Features

- Power loss reduced approx. 70% compared to the conventional
- · Low-inductance package(92.3mm x 121.7mm) adopted to deliver full SiC performance
- Package compatible with the conventional product(62mm x 108mm, 28mm terminal pitch)
- · Contributes to incereasing the output current and downsizing peripheral components by low power loss characteristics of SiC

■ Product lineup

Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)
FMF400BX-24B			4 in 1	92.3×121.7mm
RMF400DU-24B	1200V	400A	2in1 (Diode)	80×110mm
FMF400DY-24B	12000		2 in 1	62×108mm
FMF800DX-24B		800A	Z II	92.3×121.7mm







Full-SiC Power Modules for Industrial Equipment (built-in short-circuit protection function) Commercially available

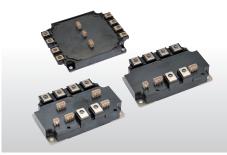
Contributes to enhancing the performance of industrial-use inverters thanks to built-in protection function for short circuit

Features

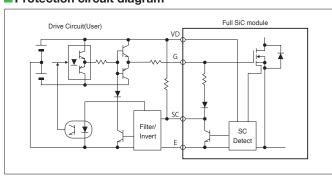
- · By using short circuit monitoring circuit in the module it is possible to transfer a short circuit detection signal to the system side
- · Power loss reduced approx.70% compared to the conventional product*
- · Low- inductance package adopted to deliver full SiC performance

■ Product lineup

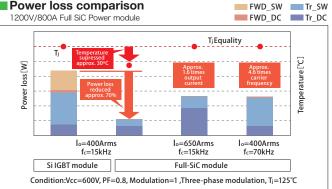
Model	Rated voltage	Rated current	Circuit configuration	Package size (D x W)		
FMF300BXZ-24B		300A	4 in 1			
FMF400BXZ-24B		400A	4 in 1	79.6×122mm		
FMF600DXZ-24B	1200V	600A	2 in 1	79.6×122mm		
FMF800DXZ-24B		800A	2 in 1			
FMF1200DXZ-24B		1200A	2 in 1	152×122mm		
FMF300DXZ-34B	1700V	300A	2 in 1	79.6×122mm		
FMF300E3XZ-34B	17000	300A	2 in 1 (Chopper)	79.0x12211111		



Protection circuit diagram



Power loss comparison



^{*}Comparison with the same rated value of the conventional 7th Gen. IGBT modules

^{*}Comparison with the same rated value of the conventional 7th Gen. IGBT modules



1200V/75A Full SiC-IPM for Industrial Equipment PMF75CGA120/PMF75CGAL120 Under development

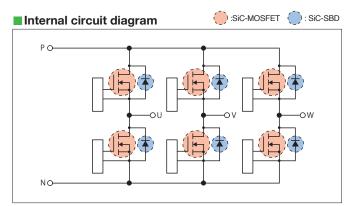
SiC chips(MOSFET and Schottky Barrier Diode) incorporated in an IPM with a built-in drive circuit and protection functions Power loss reduction of approx.70% contributes to improving the performance of industrial equipment

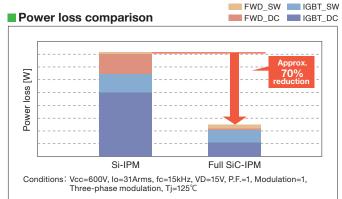
Features

- Realized high performance and low power loss by 2nd. generation SiC-MOSFET and SiC-SBD with current sense and temperature sense
- External size is reduced approx.30% with the conventional Silicon IPM products* of the same rating.
- Available to drive it by the equivalent I/F and power supply circuit with the Silicon IPM products.











Hybrid SiC Power Modules for High-frequency Switching Applications Commercially available

For optimal operation of power electronics devices that conduct high-frequency switching

Features

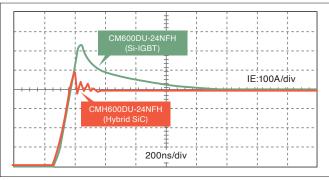
- Power loss reduction of approx. 40% contributes to higher efficiency, smaller size and weight reduction of total system
- Suppresses surge voltage by reducing internal inductance
- Package compatible with the conventional product*
- * Conventional product: Mitsubishi Electric NFH Series IGBT Modules

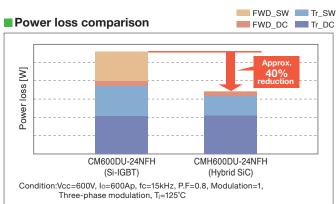
■ Product lineup

Applications	Model	Rated voltage	Rated current	Circuit configuration	External size (D x W)
	CMH100DY-24NFH		100A		48×94mm
	CMH150DY-24NFH		150A		48×94mm
	CMH200DU-24NFH		200A	2 in 1	62×108mm
Industrial equipment	CMH300DU-24NFH	1200V	300A		62×108mm
	CMH400DU-24NFH		400A		80×110mm
	CMH600DU-24NFH		600A		80×110mm
	CMH400HC6-24NFM		400A	1 in 1	62×108mm



■ Recovery waveform (FWD)







3300V Full/Hybrid SiC Power Modules for Traction Inverters and HVDC system FMF185DC-66A / FMF375DC-66A

FMF750DC-66A / FMF750DC-66A-1 / CMH600DC-66X Commercially available

Contributes to energy saving and downsizing for inverters in traction motors, DC-power transmitters, large industrial machinery

■ Features

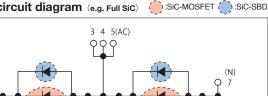
- · Suitable chip set combination for high speed switching
- · Reduced power loss compared to the conventional products*
- · Low inductance package maximize SiC perfomance
- * Si product: Mitsubishi Electric HVIGBT, CM600DC-66X

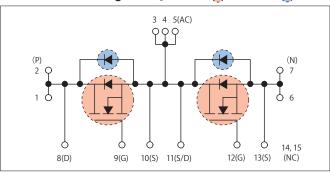
Product lineup

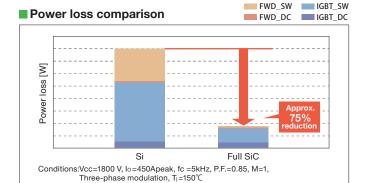
		Model	Rated Voltage	Rated Current	Circuit configuration	External size (D x W)	
		FMF185DC-66A*	3300V	185A	2 in 1		
		FMF375DC-66A		375A			
	Full SiC	FMF750DC-66A		750A		100 × 140 mm	
		FMF750DC-66A-1*(*)		750A			
	Hybrid SiC	CMH600DC-66X		600A			
	(*)Thermistor-		★:Ne	w Product			



Internal circuit diagram (e.g. Full SiC)









1700V/1200A Hybrid SiC Power Modules for Traction Inverters CMH1200DC-34S Commercially available

High-power/low-loss/highly reliable modules appropriate for use in traction inverters

Features

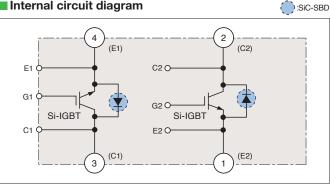
- Power loss reduced approximately 30% compared to the conventional product*
- · Highly reliable design appropriate for use in traction
- · Package compatible with the conventional product*
- * Conventional product: Mitsubishi Electric Power Module CM1200DC-34N

■ Main specifications

Module	Max.operating t	150°C	
Module	Isolation v	oltage	4000Vrms
O: IODT	Collector-emitter sa	2.3V	
Si-IGBT @150°C	Switching loss 850V/1200V	turn-on	140mJ
@ 150 0	850V/1200V	turn-off	390mJ
SiC-SBD	Emitter-collect	2.3V	
@150°C	Capacitive	9.0µC	



Internal circuit diagram



FWD SW IGBT_SW Power loss comparison FWD_DC IGBT_DC ≥ loss CMH1200DC-34S CM1200DC-34N Condition: Vcc=850V, Io=600Arms, fc=1kHz, P.F=1, Modulation=1, Three-phase modulation, T_j=125°C



600V/15A,25A Full SiC Super mini DIPIPM™ for Home Appliances

PSF15S92F6-A6/PSF25S92F6-A6 Commercially available

Contributes to extremely high power-efficiency in air conditioners, and easily applicable to industrial equipment

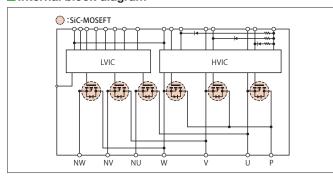
■ Features

- · SiC-MOSFET achieves reduction in ON resistance, power loss reduced approx. 70% compared to conventional product*
- · Construct low-noise system by reducing recovery current
- Numerous built-in functions: Bootstrap diode for power supply to drive P-side, temperature
- · Unnecessary minus-bias gate drive circuit using original high Vth SiC-MOSFET technology
- · As package and pin layout compatibility with conventional products* is ensured, simply replace with this product to improve performance *Conventional product: Mitsubishi Electric Super mini DIPIPM Series

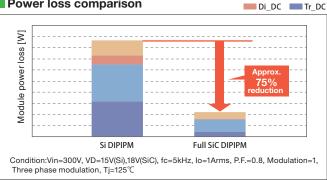


Di_SW Tr_SW

Internal block diagram



■ Power loss comparison



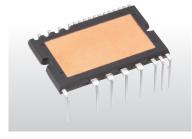


Full SiC Super mini DIPPFC™ for Home Appliances PSF30L92A6-A Commercially available

Utilizing SiC enables high-frequency switching and contributes to reducing the size of peripheral components

■ Features

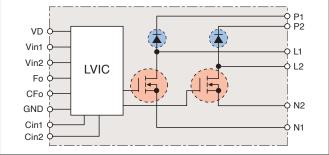
- · Incorporating SiC chip in the Super mini package widely used in home appliances
- The SiC chip allows high-frequency switching (up to 40kHz) and contributes to downsizing the reactor, heat sink and other peripheral components
- · Adopts the same package as the Super mini DIPIPM to eliminate the need for a spacer between the inverter and heat sink, and to facilitate its implementation



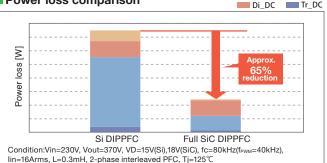
Di_SW

Tr_SW

■ Internal block diagram (PSF30L92A6-A) (SiC-MOSFET (SiC-SBD



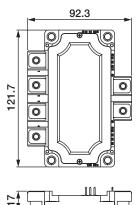
Power loss comparison



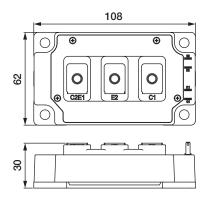
Outline Drawing of SiC Power Modules

Unit:mm

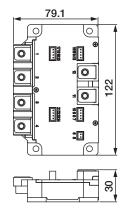




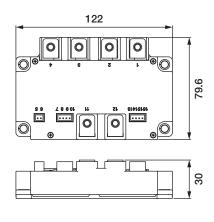
Full SiC Power Modules for Industrial Equipment FMF400DY-24B



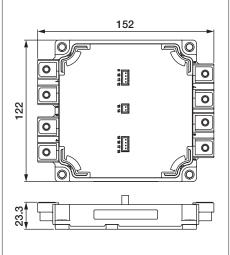
Full SiC Power Modules for Industrial Equipment FMF300BXZ-24B FMF400BXZ-24B



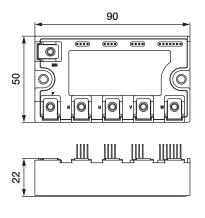
Full SiC Power Modules for Industrial Equipment FMF600DXZ-24B/FMF800DXZ-24B FMF300DXZ-34B/FMF300E3XZ-34B



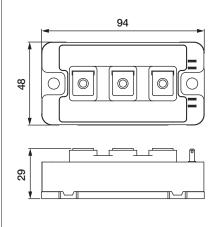
Full SiC Power Modules for Industrial Equipment FMF1200DXZ-24B



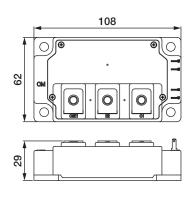
Full SiC IPM for Industrial Equipment PMF75CGA120 PMF75CGAL120



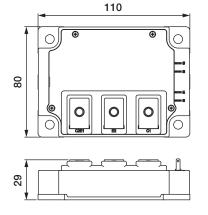
Hybrid SiC Power Modules for High-frequency Switching Applications CMH100DY-24NFH CMH150DY-24NFH



Hybrid SiC Power Modules for High-frequency Switching Applications CMH200DU-24NFH CMH300DU-24NFH



Hybrid SiC Power Modules for High-frequency Switching Applications CMH400DU-24NFH CMH600DU-24NFH Full SiC Power Modules for Industrial Equipment RMF400DU-24B

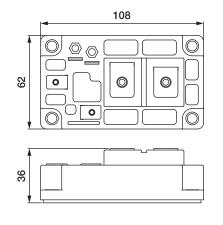


SiC Power Modules

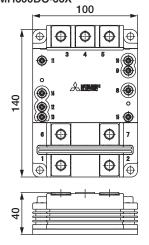
Outline Drawing of SiC Power Modules

Unit:mm

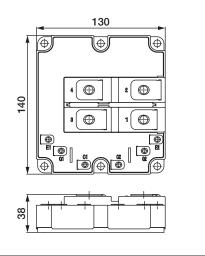




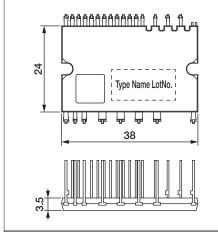
3300V Full/Hybrid SiC Power Modules for Traction Inverters and HVDC system FMF185/375/750DC-66A FMF750DC-66A-1 CMH600DC-66X



1700V/1200A Hybrid SiC Power Module for Traction Inverters CMH1200DC-34S



Full SiC Super mini DIPIPM™
PSF15S92F6-A6/PSF25S92F6-A6
Full SiC Super mini DIPPFC™
PSF30L92A6-A
Long



Package, Main Application

Package		Main application
SOPIPM	-	Fan motor
SLIMDIP	_	Air conditioner/Fan motor/Washing machine/Refrigerator
Super mini	-	Air conditioner/Washing machine/Servo/Robot
Mini	—	Air conditioner/Motion control
Large	-	Commercial air conditioner/Motion control
DIPIPM+	-×	Commercial air conditioner/Motion control
Large DIPIPM+		Commercial air conditioner/Motion control

Data sheet here



Rated Lineup

			Rated current										
		2A	5A	10A	15A	20A	25A	30A	35A	40A	50A	75A	100A
Rated	600V							•			*		
voltage	1200V			*			*		*			• • • • • • • • • • • • • • • • • • •	



Featured Products

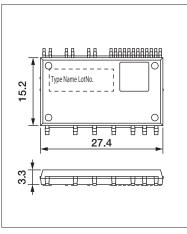


Surface mount package IPM SOPIPM

A small surface mount package IPM enables easy system design by enough insulation distance and protection function for fan and low-power motor drive applications

- <Main Features>
- •Optimal pin layout realizes easier PCB wiring design and enables smaller PCB size
- •Insulation distance between pins ensured, realizing easier board mounting without coating process
- •Newly integrated interlock function in addition to conventional protection features for robust operation
- •Installing RC-IGBT¹ simultaneously realizes compact package and low loss performance can go thogether
- •Bootstrap diode is integrated for the P-side drive power supply like conventional DIPIPM series, reducing the number of peripheral external parts

Outline Drawing



■SOPIPM

Type name	Rated voltage Rated current		Chips	Protection	Shape	
SP2SK	600V	2A	RC-IGBT, HVIC, LVIC, BSD	UV, SC, ОТ Voт, IL	Surface mount package	

[Term] UV: Power supply Under Voltage protection

 $\begin{array}{l} \text{SC} : \text{Short Circuit protection} \\ \text{OT} : \text{Over Temperature protection} \\ \text{V}_{\text{OT}} : \text{Analog Temperature Output} \end{array}$

IL : Inter Lock

^{*1} Reverse-conducting IGBT



Featured Products

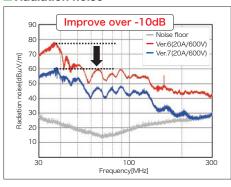
New design with expanded operating temperature range and lower noise contributes to easier system design and reduction in system cost

Super Mini DIPIPM Ver.7

<Main Features>

- •New low-noise 7th-generation CSTBT*1 incorporated, keeping same efficiency as DIPIPM Ver.6 Series. System cost reduction for noise suppression parts achieved.
- Maximum junction temperature range expanded to 175°C, supporting instantaneous overcurrent capability at overload operation
- •Wider terminal base shape contributes to improved terminal strength and suppresses increase in temperature
- ·High compatibility for terminal layout, easy to replace from the conventional series
- *1 CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

■ Radiation noise





Featured Products

Expanded line up for SLIMDIP series contributes system cost down for home appliances and fan drive application.

SLIMDIPTM

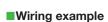
SLIMDIP-S, SLIMDIP-M, SLIMDIP-L, SLIMDIP-W, SLIMDIP-X, SLIMDIP-Z

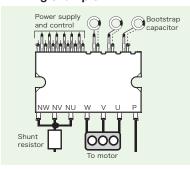
<Main Features>

- •RC-IGBT*¹ incorporated, reducing package size 30% compared to Super mini DIPIPM
- •Maximum case temperature expanded to 115°C, increasing the operating temperature range and leading to easier system design temperature range and leading to easier system design
- Additional terminals for floating supply and built-in bootstrap diodes simplify PCB wiring pattern
- •Both V_{OT} 2 and OT 3 functions integrated for temperature protection
- •Expanded lineup accommodates wide-ranging inverter capacities

Product lineup

Type name	Main application
SLIMDIP-S	Fan, refrigerator
SLIMDIP-M	Fan, washing machine
SLIMDIP-L	Air conditioner
SLIMDIP-W	Washing machine, Fan
SLIMDIP-X	Air conditioner
SLIMDIP-Z	Air conditioner







Customer Support

EVA Series evaluation boards for each DIPIPM Series to support system design

*1 Reverse conducting IGBT *2 Vot : Analog Temperature Output *3 OT : Over Temperature protection



For Super mini DIPIPM EVA11-SDIP



For DIPIPM+ EVA14-DIP+



For SOPIPM EVA18-SOP



For Large DIPIPM Series (Microcomputer-embedded demonstration board) EVA20-LDIP

^{*} For further information, please contact sales office

Series Matrix of 600V DIPIPM

	Vces				600V			
	Series	OL IMPLE	Supe	r mini	M	lini	Large	DIPIPM+
1	c	SLIMDIP	Ver.7	Ver.6	Ver.7	_	Ver.6	CIB/CI
	5A	SLIMDIP-S		PSS05S92F6-AG PSS05S92E6-AG		PSS05S51F6		
	10A	SLIMDIP-M		PSS10S92F6-AG PSS10S92E6-AG		PSS10S51F6		
	15A	SLIMDIP-L SLIMDIP-W	PSS15S93F6-AG PSS15S93E6-AG	PSS15S92F6-AG PSS15S92E6-AG		PSS15S51F6		
	20A	SLIMDIP-X	PSS20S93F6-AG PSS20S93E6-AG	PSS20S92F6-AG PSS20S92E6-AG	PSS20S73F6	PSS20S51F6 PSS20S71F6		
	30A	SLIMDIP-Z*	PSS30S93F6-AG PSS30S93E6-AG	PSS30S92F6-AG PSS30S92E6-AG	PSS30S73F6	PSS30S71F6		
	35A			PSS35S92F6-AG PSS35S92E6-AG				
	40A		PSS40S93F6-AG PSS40S93E6-AG					
	50A				PSS50S73F6	PSS50S71F6	PSS50SA2F6	PSS50MC1F6 PSS50NC1F6*5
	75A						PSS75SA2F6	
	Chip	RC-IGBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
9_	UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side	P-side/ N-side/ Brake
Ęġ.	SC	N-side	N-side	N-side	N-side	N-side	N-side with sense	N-side
Protective Function	ОТ	N-side	N-side*1	N-side*1	_	_	_	_
	VOT	N-side	N-side*1	N-side*1	N-side	N-side	N-side	N-side
	Active input	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(3/5V)	High(5V)
	Emitter pin of N-side	Open	Open	Open	Open	Open	Open	Open
ons	Fault output	N-side(UV,SC,OT)	N-side (UV,SC,OT)	N-side(UV,SC,OT)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
Specifications	Insulation voltage	2000Vrms*2	1500Vrms*2	1500Vrms*2	2500Vrms	2500Vrms	2500Vrms	2500Vrms
cifi	Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Molding resin*4/Insulation sheet	Insulation sheet	Insulation sheet
Spe	RoHS directive*6	Compliant	Compliant	Compliant	Compliant	Compliant*3	Compliant	Compliant
	Pin type*7	Control side of Zigzag (Normal, Short)	Long	Long	Short	Control side of Zigzag, Short	_	_

- [Notes] $\,$ *1 : PSSxxS9xE6 has OT function, PSSxxS9xF6 has V_{OT} function
 - *2 : AC60Hz,1minute.Corresponds to isolation voltage 2500Vrms in the case the convex-shaped heat sink
 - *3 : High melting point solder (Lead Over 85%) is used for chip soldering of PSSxxS51F6 only.
 - *4: Molding resin insulation for PSSxxS51F6/-C

 - *5: PSS50NC1F6 is not included brake. *6: RoHS directive (2011/65/EU and (EU) 2015/863)
 - *7 : Refer the datasheet of each product for more detail

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

RC-IGBT: Reverse conducting IGBT

HVIC: High Voltage IC

UV: Power supply Under Voltage protection OT: Over Temperature protection

SC: Short Circuit protection

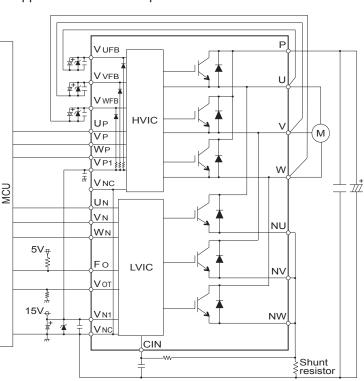
Vot: Analog Temperature Output

RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

CIB: Converter Inverter Brake,

CI: Converter Inverter

Application circuit of super mini DIPIPM



★: New Product

Lineup of DIPIPM™

Series Matrix of 1200V DIPIPM

	V _{CES}			1200V		
	Series	M	ini	Large	DIPIPM+	Large DIPIPM+
I	c	Ver.7	_	Ver.6	CIB/CI	CI
	5A	PSS05S73FT	PSS05S72FT	PSS05SA2FT	PSS05MC1FT PSS05NC1FT*1	
	10A	PSS10S73FT	PSS10S72FT	PSS10SA2FT	PSS10MC1FT PSS10NC1FT*1	
	15A	PSS15S73FT		PSS15SA2FT	PSS15MC1FT PSS15NC1FT*1	
	25A	PSS25S73FT		PSS25SA2FT	PSS25MC1FT PSS25NC1FT*1	
	35A			PSS35SA2FT	PSS35MC1FT PSS35NC1FT*1	
	50A			PSS50SA2FT		PSS50NE1CT
	75A			PSS75SA2FT		PSS75NE1CT
	100A					PSS100NE1CT
	Chip	CSTBT	CSTBT	CSTBT	CSTBT	CSTBT
9c	UV	P-side/N-side	P-side/N-side	P-side/N-side	P-side/N-side/Brake	P-side/N-side
Protective Function	SC	N-side	N-side	N-side	N-side	N-side
ote	ОТ	_	_	_	_	_
갶	Vот	N-side	N-side	N-side	N-side	N-side
	Active input	High(5V)	High(5V)	High(5V)	High(5V)	High(3/5V)
US	Emitter pin of N-side	Open	Open	Open	Open	Open
Specifications	Fault output	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)	N-side (UV,SC)
ξį	Insulation voltage	2500Vrms	2500Vrms	2500Vrms	2500Vrms	2500Vrms
eci	Insulation structure	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet	Insulation sheet
Sp	RoHS directive*2	Compliant	Compliant	Compliant	Compliant	Compliant
	Pin type	_	_	_	_	_

[Notes] *1: PSS**NC1FT is not included brake

*2: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

UV: Supply Under Voltage protection OT: Over Temperature protection SC: Short Circuit protection

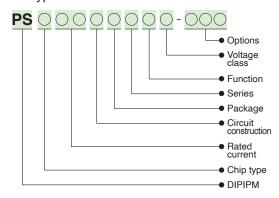
VOT: Analog Temperature Output

RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

CIB: Converter Inverter Brake

CI: Converter Inverter

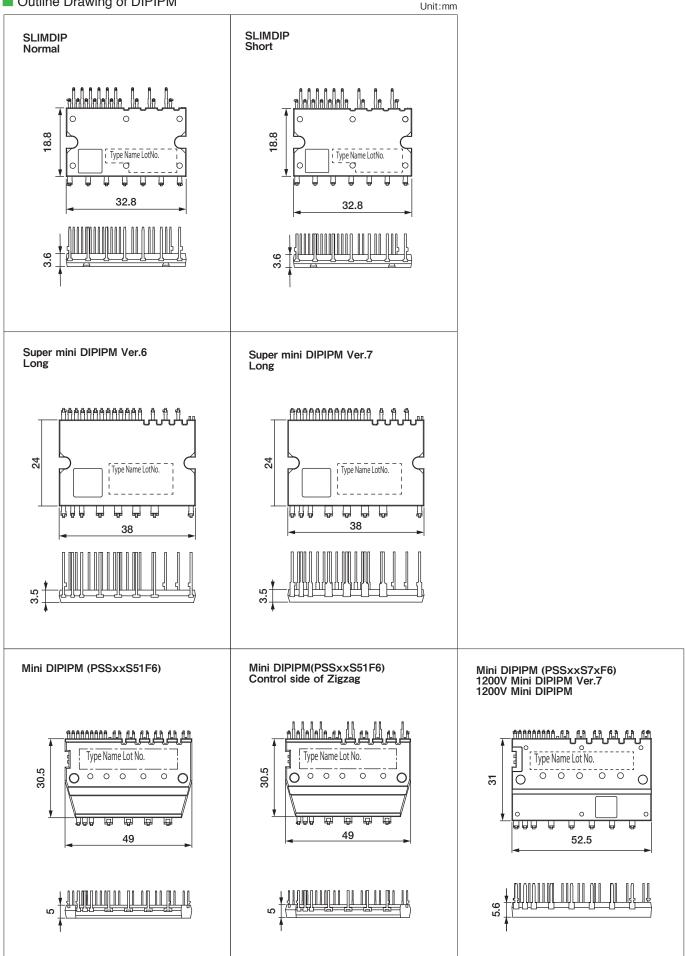
■ Type Name Definition of DIPIPM



Lineup of DIPIPM™



Unit:mm



Lineup of DIPIPM™

Outline Drawing of DIPIPM

Unit:mm Large DIPIPM Large DIPIPM+ DIPIPM+ Type Name Lot No. Type Name Lot No. 31 34 43 0 114.5

Series, Main Application

	Series	Main Application
G1	•	Motion control/Renewable energy/Power supply
V1	—	Motion control/Renewable energy/Power supply

Data sheet here



Rated Lineup

		Rated current												
		25A	35A	50A	75A	100A	150A	200A	300A	400A	450A	500A	600A	800A
	600V									*				
Rated voltage	650V										•			
	1200V				•						•			



Featured Products

Loaded with built-in functions, contributing to inverters with enhanced energy savings





- •Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT™¹ and a diode incorporating a RFC¹² structure that contributes to reducing the power consumed in inverters
- •The new resin-insulated metal baseplate, originally introduced in 7th-generation IGBT modules, eliminates the solder-attached section, increasing the thermal cycle lifetime and improving inverter reliability
- In addition to the built-in functions of the previous product, automatic switching speed control, and error detection function contribute to lowering inverter loss and shortening design time
- *1 CSTBT: Mitsubishi Electric's unique IGBT that utilizes the carrier cumulative effect
- *2 RFC: Relaxed field cathode
- *3 Conventional product: IPM L1-Series

Built-in functions: Supply Undervoltage lock protection (UV), Short-circuit protection (SC), Over-temperature protection (OT)

"A" package main pin shape and layout

For the "A" package 6-in-1 (CG1A) main pin shape, select either solder pin or screw type For the pin layout, select either straight or L-shaped

Main pin shape









Main pin: Solder pin

Main pin: Screw

L-shaped

Lineup of IPM

Matrix of IPM 650V/600V (No.: Number of outline drawing, see page 21)

	No
Connection	No.
D	01
D	01
D	02

[Notes] *1: Full-gate CSTBT $^{\text{TM}}$ *2: PCM (Plugged Cell Merged) CSTBT $^{\text{TM}}$ *3: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] UV: Power supply Under Voltage protection SC: Short Circuit protection OT: Over Temperature protection

RoHS: Restriction of hazardous substances in electrical and electronic equipment

Lineup of IPM

Matrix of IPM 1200V (No.: Number of outline drawing, see page 21)

Vces			120	00V		
Series	G1 Series	Connection	No.	V1 Series	Connection	No.
	PM25CG1A120	С	06			
	PM25CG1B120	С	04			
	PM25RG1A120	R	06			
25A	PM25RG1B120	R	04			
ZJA	PM25CG1AL120	С	06			
	PM25CG1AP120	С	03			
	PM25CG1APL120	С	03			
	PM25RG1AP120	R	03			
	PM35CG1A120	С	06			
	PM35CG1B120	С	04			
	PM35RG1A120	R	06			
35A	PM35RG1B120	R	04			
SSA	PM35CG1AL120	С	06			
	PM35CG1AP120	С	03			
	PM35CG1APL120	С	03			
	PM35RG1AP120	R	03			
	PM50CG1A120	С	06			
	PM50CG1B120	С	04			
504	PM50RG1B120	R	04			
50A	PM50CG1AL120	С	06			
	PM50CG1AP120	С	03			
	PM50CG1APL120	С	03			
	PM75CG1B120	С	04			
75A	PM75RG1B120	R	04			
			٠.			
	PM100CG1B120	С	04			
4004	PM100CG1C120	С	05			
100A	PM100RG1B120	R	04			
	PM100RG1C120	R	05			
	PM150CG1C120	С	05			
150A	PM150RG1C120	R	05			
	DM0000040400					
200A	PM200CG1C120	С	05	PM200DV1A120	D	01
	PM200RG1C120	R	05	DM000DW A400		
300A 450A				PM300DV1A120 PM450DV1A120	D D	01
430A	CSTBT*1			CSTBT*1	D	
IGBT	Emitter sensor installed			Built-in current sensor		
chip	Temperature sensor installed			Built-in temperature sensor		
UV	P-side/N-side			P-side/N-side		
Fault OT output	P-side/N-side			P-side/N-side		
SC	P-side/N-side			P-side/N-side		
Identification	P-side/N-side			_		
RoHS directive*3	Compliant			Compliant		
Compatibility				V Series		
Connection	D C R					

[Notes] *1: Full-gate CSTBT™ *2: PCM (Plugged Cell Merged) CSTBT™ *3: RoHS directive (2011/65/EU and (EU) 2015/863)

[Term] CSTBT™: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect UV: Power supply Under Voltage protection SC: Short Circuit protection OT: Over Temperature protection

RoHS: Restriction of the use of certain Hazardous Substances in electrical and electronic equipment

Lineup of IPM

Outline Drawing of IPM Unit:mm 02 03 PM400,600DV1A060 PM200,300,450DV1A120 PM800DV1B060 PM50,75,100CG1AP/CG1APL065 PM50,75RG1AP065 PM25,35,50CG1AP/CG1APL120 PM25,35RG1AP120 120 120 90 **●**(○ ଠା• (A) 0 7 11 11 11 11 11 11 11 11 90 20 $(\bigcirc$ 50 0 0 0 0 0 0 34 04 06 05 PM50,75,100,150,200CG1B/ RG1B065 PM25,35,50,75,100CG1B/ RG1B120 PM200,300,450CG1C/ PM50,75,100CG1A/CG1AL065 RG1C065 PM100,150,200CG1C/ RG1C120 PM50,75RG1A065 PM25,35,50CG1A/CG1AL120 PM25,35RG1A120 120 120 90 10 0 •••• ••• ••• 0 0 0 55 $(\bigcirc$ @····||||····||||....|| 85 ((O 20 0 $\bigcirc)$ O О 0 0 0 o 22 ЩЩ 22

Series, Main Application

Series		Main Application
Т	-	
T1	_	
TH	-	Motion control/Renewable energy /Power supply
For 3-level Inverters	—	
S	-	

Data sheet



Rated Lineup





New Products

Industrial IGBT module with new standard package "LV100" for high power density inverter

IGBT module T-series (LV100 for industrial)

IGBT module 2in1 type

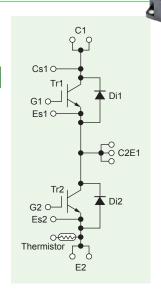
Lineup

1200A/2000V

 $800A/1700V,\,800A/1700V(with enhanced FWD),\,1200A/1700V\,800A/1200V,\,1200A/1200V$

$\langle {\rm Main \ Features} \rangle$

- Next generation high capacity standard package for industrial use
- •Improved ease of use by applying low impedance package
- •Reducing the switching loss and optimal for the applications that are used in 1 to 5KHz
- Isolation voltage 4kV





Featured Products

New lineup contributes to simple design downsizing, energy-savings of industrial inverters.

IGBT Module T/T1-Series

- ·New modules equipped with three-phase converter, inverter, and brake circuit(CIB), contributes to simplifying design for inverter systems
- •CIB modules contribute to compact inverter systems by reducing package size by 36% compared to the Mitsubishi Electric's existing module.(CIB)
- · Power loss has been reduced with the introduction of the 7th-generation IGBT produced using CSTBT2 and a diode incorporating a relaxed field of cathode (RFC) structure
- · The new structure introduced eliminates the solder-attached section, increasing the thermal cycle lifetime, which contributes to improving the reliability of inverters
- The introduction of press-fit pins and PC-TIM^{*1} contribute to simplifying the assembly process for inverters
- *1 PC-TIM: Phase change thermal interface material *2 CSTBT: Mitsubishi Electric's unique IGBT that makes use of the carrier cumulative effect

Press-fit terminal support(NX)

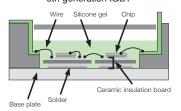
- · Possible to select the control pin shape (soldered terminals/press-fit terminals)
- · Solder attachment process eliminated



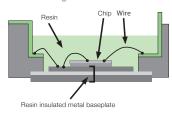


New structure realizes improved reliability (improved thermal cycle lifetime)

NX package structure comparison 6th-generation IGBT

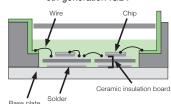


7th-generation IGBT

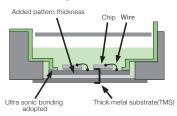


Adopts SoLid Cover(SLC) Technology

Compared to standard (std) package structure 6th-generation IGBT



7th-generation IGBT



Standard package is not available for CIB

Featured Products

Low switching loss contributes to efficiency improvement of industrial inverters during high-frequency operation.

TH-series IGBT Modules with 7th-generation IGBT for High-frequency switching applications

<Main Features>

- ·A chip optimized for high-frequency applications fc target 20-60kHz
- ·High-speed specifications reduce power consumption during high-frequency switching. The loss is reduced by about 30% compared to general specifications*1
- ·Lineup of 1200V 200A to 600A (2 types of packages are available for 400A)
- *1:7th-generation T series with general specifications

Package



48 x 94mm 1200V/200A •CM200DY-24TH



62 x 108mm 1200V/400A •CM400DY-24TH



80 x 110mm 1200V/400A,600A •CM400DU-24TH

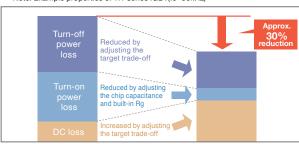
·CM600DU-24TH

Type name	Rated Voltage	Rated Current	Connection	External size (D x W)
CM200DY-24TH		200A		48.0 x 94.0mm
CM400DY-24TH	1200V	400A	2 in 1	62.0 x 108.0mm
CM400DU-24TH	12000	400A	2 111 1	80.0 x 110.0mm
CM600DU-24TH		600A		80.0 X 110.0mm

Power loss comparison

■ Product lineup

Note: Example properties of TH-series IGBT(fc=30kHz)



general specifications 7th-generation T-series

High-speed specifications 7th-generation TH-series

Matrix of IGBT Modules 650V/600V (No.: Number of outline drawing, see page 27 to 31)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

Vces		600V							
Series	T/T1-Series			T-Series			NFH-Series		
lc	NX Type	Connection	No.	std Type	Connection	No.	NFH-Selles	Connection	No.
50A	CM50MXUB-13T CM50MXUB-13T1 CM50MXUBP-13T CM50MXUBP-13T1	M M M	32 32 36 36						
75A	CM75MXUB-13T CM75MXUB-13T1 CM75MXUBP-13T CM75MXUBP-13T1	M M M	32 32 36 36						
100A	CM100TX-13T CM100TXP-13T CM100MXUB-13T CM100MXUB-13T1 CM100MXUBP-13T CM100MXUBP-13T1 CM100MXUD-13T CM100MXUD-13T1 CM100MXUD-13T1 CM100MXUDP-13T	T M M M M M M	24 27 32 32 36 36 34 34 38 38	CM100DY-13T	D	19			
150A	CM150TX-13T CM150TXP-13T CM150RX-13T CM150RXP-13T CM150MXUD-13T CM150MXUD-13T1 CM150MXUDP-13T CM150MXUDP-13T1	T T R R M M	24 27 25 28 34 34 38 38	CM150DY-13T	D	19			
200A	CM200TX-13T CM200TXP-13T CM200RX-13T CM200RXP-13T	T T R	24 27 25 28	CM200DY-13T	D	19	CM200DU-12NFH	D	11
300A	CM300DX-13T CM300DXP-13T	D D	17 29	CM300DY-13T	D	20	CM300DU-12NFH	D	12
400A				CM400DY-13T	D	20	CM400DU-12NFH	D	12
450A	CM450DX-13T CM450DXP-13T	D D	17 29						
600A	CM600DX-13T CM600DXP-13T	D D	17 29	CM600DY-13T	D	21	CM600DU-12NFH	D	13
Connection	D T WIND	R		M M					

Matrix of Power Modules for 3-level Inverter (No.: Number of outline drawing, see page 27 to 31)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

VCES/VRRM	1200 V IGB	T Module		1700 V IGBT	Modul	Э	1200 V Dioc			1700 V Dio		
lc/lF	T/S-Series std Type	Connection	No.	S-Series std Type	Connection	n No.	S-Series std Type	Connection	n No.	S-Series std Type	Connection	No.
		OOTHICCTION	INO.		OOI II ICCEII	III INO.		Oorniccti	INO.		Oornicction	INO.
400A	CM400C1Y-24S	C1	09									
450A	CM450C1Y-24T	C1	21									
500A	CM500C2Y-24S	C2	26									
600A	CM600C1Y-24T	C1	21	CM600HA-34S	Н	26				RM600DY-34S	D	22
800A				CM800HA-34S	Н	26				RM800DY-34S	D	22
1000A				CM1000HA-34S	Н	26						
1400A	CM1400HA-24S	Н	26				RM1400HA-24S	Н	26			
Connection	IGBT module C1		c	H S	- [Å] - [Å] - [Å]	•	Diode module	Н	D			

Matrix of IGBT Modules 1200V (No.: Number of Outline Drawing, see page 27 to 31)

RoHS directive (2011/65/EU, (EU)2015/863) compliant

Vces 1200V														2015/863) cor							
Series	T-Series LV100			T/T1-Series NX			T-Series std T			TH-Series			S-Series NX T			S-Series std Ty		_	S-Series MPD Ty		
lc \	Connec	ction	No.			_	Connec	tion	No.	Connec	tion	No.	Connec	tion	No.	Connec	tion	No.	Connect	tion	No.
35A				CM35MXUA-24T CM35MXUA-24T1 CM35MXUAP-24T CM35MXUAP-24T1	M M	31 31 35 35							CM35MXA-24S	М	03						
50A				CM50MXUA-24T CM50MXUA-24T1 CM50MXUAP-24T CM50MXUAP-24T1	M M	31 31 35 35							CM50MXA-24S	М	03						
75A				CM75MXUB-24T CM75MXUB-24T1 CM75MXUBP-24T CM75MXUBP-24T1 CM75MXUC-24T CM75MXUC-24T1 CM75MXUC-24T1 CM75MXUCP-24T1	M M M M M	32 36 36 33 33 37 37							CM75MXA-24S CM75TX-24S CM75RX-24S	Т	03 04 01						
100A				CM100TX:24T CM100TXP:24T CM100FX:24T CM100FXP:24T CM100MXUC:24T CM100MXUC:24T CM100MXUC:24T1 CM100MXUCP:24T1	T R R M M	24 27 25 28 33 33 37 37	CM100DY-24T	D	19				CM100MXA-24S	М	03						
150A				CM150TX-24T CM150TXP-24T CM150RXP-24T CM150RXP-24T CM150MXUD-24T CM150MXUD-24T1 CM150MXUDP-24T1 CM150MXUDP-24T1	T R R M	24 27 25 28 34 34 38 38	CM150DY-24T	D	19				CM150DX-24S CM150EXS-24S		02 16						
200A				CM200TX-24T CM200TXP-24T	T T	24 27	CM200DY-24T	D	20	CM200DY-24TH	D	06	CM200EXS-24S CM200RXL-24S CM200DX-24S	R	16 15 02						
225A				CM225DX-24T CM225DXP-24T CM225DX-24T1 CM225DXP-24T1	D D	17 29 17 29															
300A				CM300DX-24T CM300DXP-24T CM300DX-24T1 CM300DXP-24T1	D D	17 29 17 29	CM300DY-24T	D	20				CM300EXS-24S	Е	16	CM300DY-24S	D	07			
400A										CM400DY-24TH CM400DU-24TH		08 13									
450A				CM450DX-24T CM450DXP-24T CM450DX-24T1 CM450DXP-24T1	D D	17 29 17 29	CM450DY-24T	D	21							CM450DY-24S	D	09			
600A				CM600DX-24T CM600DXP-24T CM600DX-24T1 CM600DXP-24T1	D D	17 29 17 29	CM600DY-24T	D	21	CM600DU-24TH	D	13	CM600DXL-24S	D	05	CM600DY-24S	D	09			
800A	CM800DW-24T	D	39	CM800DX-24T1 CM800DXP-24T1		17 29										CM800DY-24S	D	10	OMOGODUG		4.
900A				CM1000DX-24T	D	18							OM1000DVI 040	7	05				CM900DUC-24S	ט	14
1000A		_		CM1000DXP-24T		30							CM1000DXL-24S	ט	05						_
1200A 1400A	CM1200DW-24T	D	39													CM1400HA-24S	Н	26	CM1400DUC-24S	D	14
Connection	H	1	1				F					M		1 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0 0		E		~ 0	E3		

 $^{{\}rm *1:A-Series\; have\; model\; namse\; ending\; with\; A,\; NF-Series\; have\; model\; name\; ending\; with\; NF/NFH}$

^{*2:} std Type have model name "CM**DY/HA-24S, MPD Type have model name "CM**DUC-24S"

Matrix of IGBT Modules 1700V(No.: Number of Outline Drawing, see page 27 to 31)

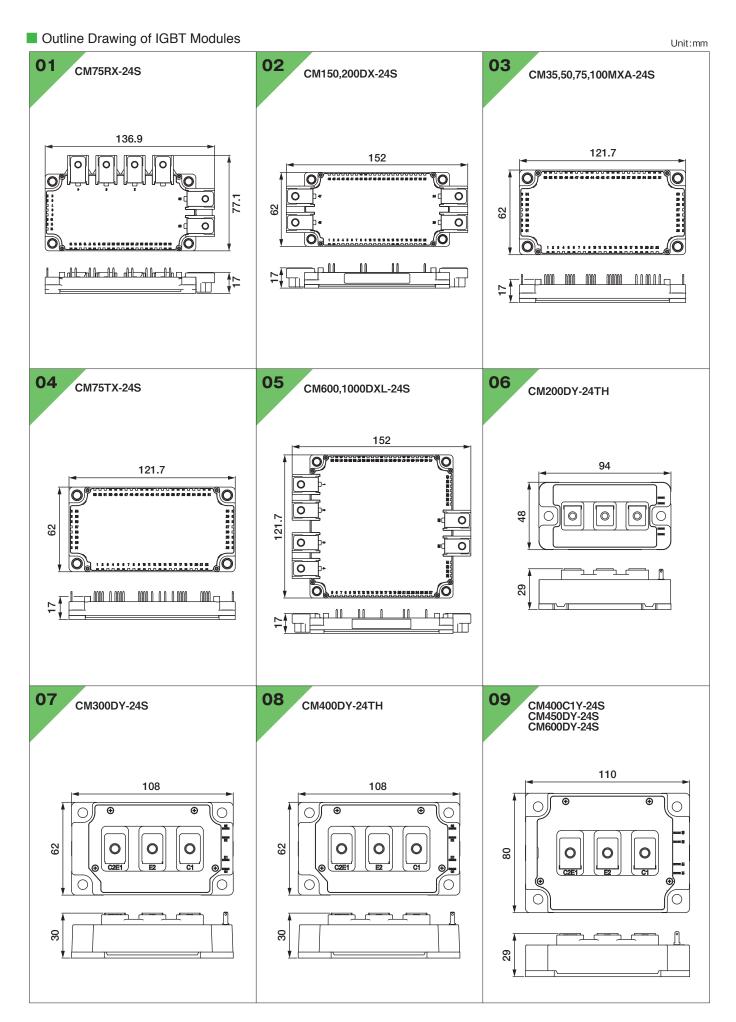
RoHS directive (2011/65/EU, (EU)2015/863) compliant

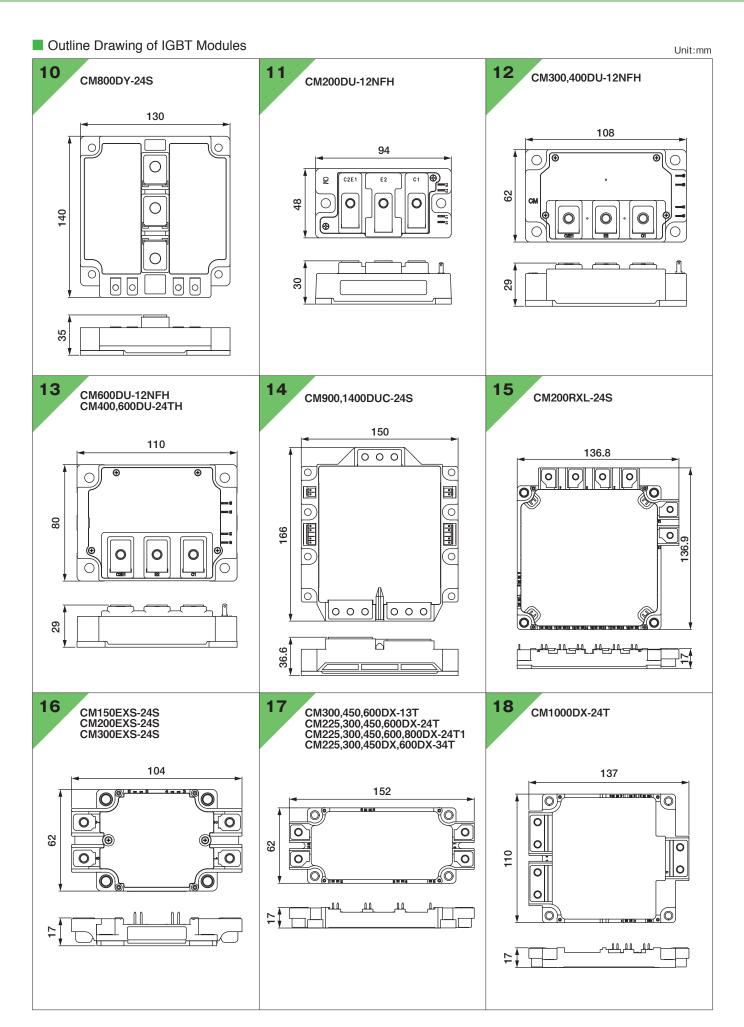
Vces						170	00V					
Series I _C	T-Series LV100 Type	Connection	No.	T-Series NX Type	Connection	No.	T-Series std Type	Connection	No.	S-Series std Type	Connection	No.
75A							CM75DY-34T	D	19			
100A				CM100TX-34T CM100TXP-34T	T T	24 27	CM100DY-34T	D	19			
150A				CM150TX-34T CM150TXP-34T	T T	24 27	CM150DY-34T	D	20			
200A							CM200DY-34T	D	20			
225A				CM225DX-34T CM225DXP-34T	D D	17 29						
300A				CM300DX-34T CM300DXP-34T	D D	17 29	CM300DY-34T	D	21			
400A							CM400DY-34T	D	21			
450A				CM450DX-34T CM450DXP-34T	D D	17 29						
500A												
600A				CM600DX-34T CM600DXP-34T	D D	17 29				CM600HA-34S	Н	26
800A	CM800DW-34T CM800DW-34TA	D D	39 39							CM800HA-34S	Н	26
1000A										CM1000HA-34S	Н	26
1200A	CM1200DW-34T	D	39									
Connection	Н	D		T old	R		M		ار مار مار مار	E		:

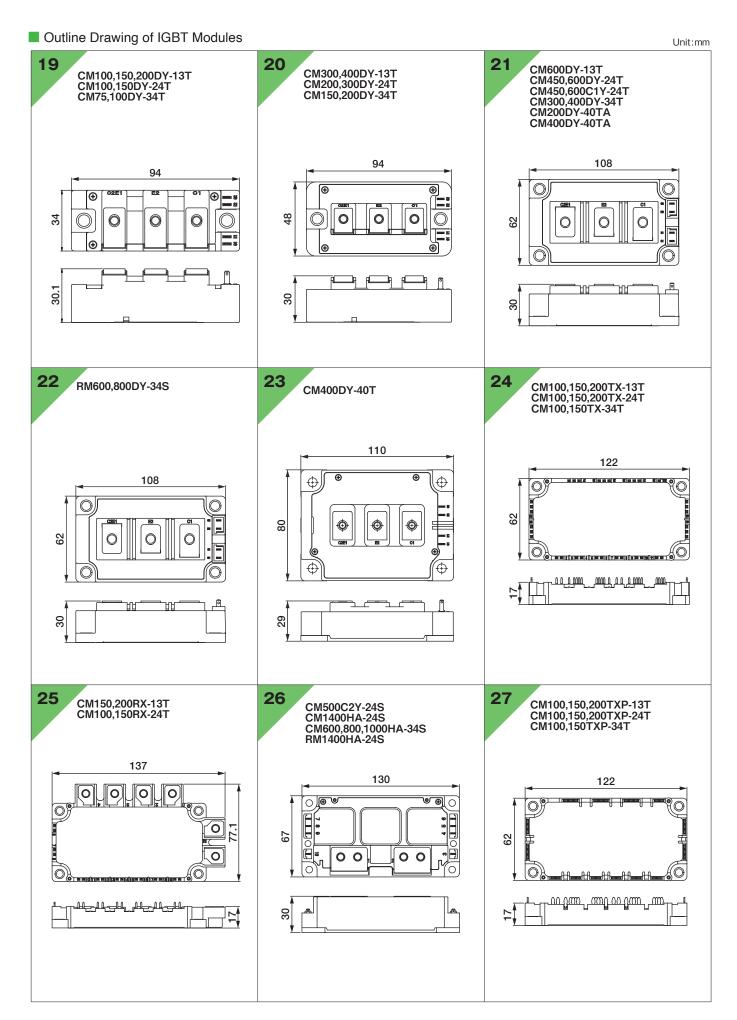
Matrix of IGBT Modules 2000V(No.: Number of Outline Drawing, see page 27 to 31)

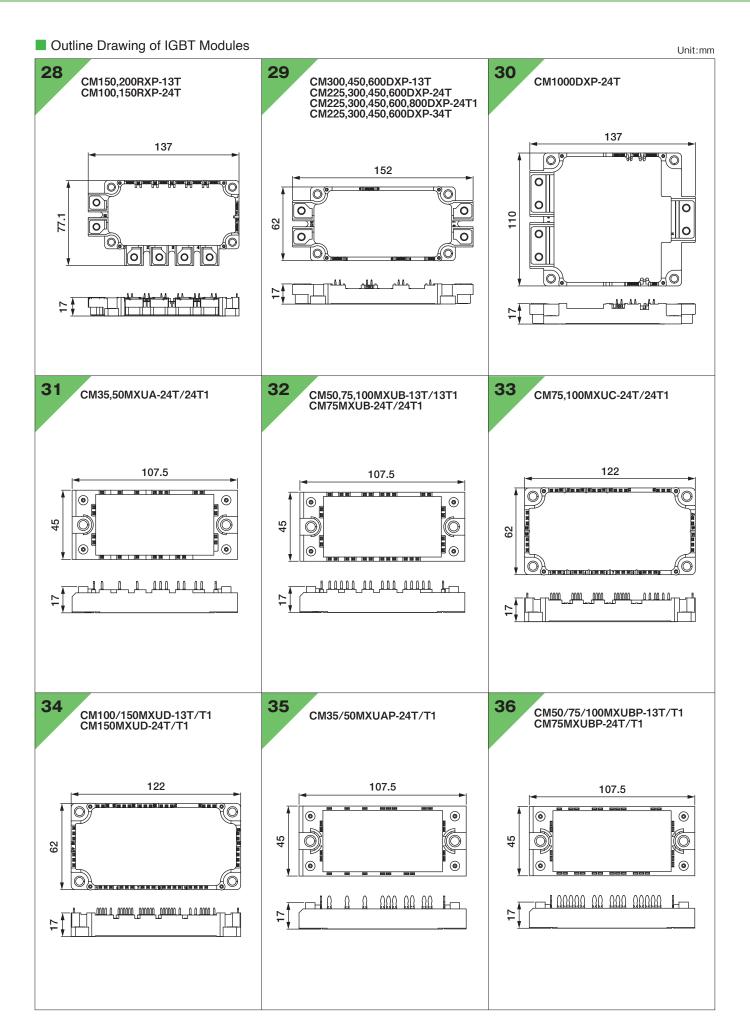
RoHS directive (2011/65/EU, (EU)2015/863) compliant

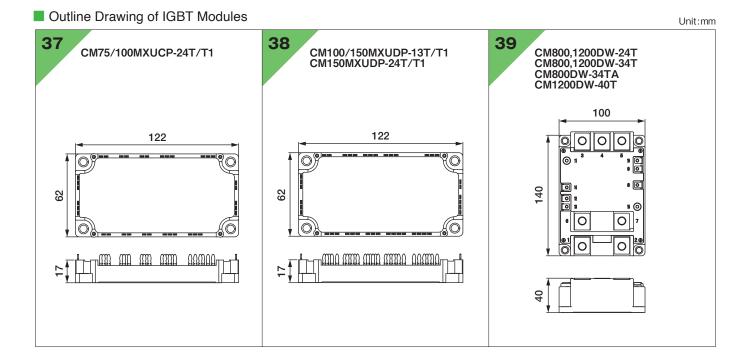
Vces				200)OV						
Series	T-Series	T-Series LV100 Type T-Series std T									
Ic		Connec	tion No.			Connec	tion	No.			
200A					CM200DY	D	21				
400A					CM400DY CM400DY		D D	23 21			
1200A	CM1200D	W-40T	D	39							
Connection			1	D							











Series, Main Application

	Series	Main Application
Χ	-	
R		
S	-	Traction/Power transmission/Motion control
N	—	
Н		

Data sheet here



Rated Lineup

		Rated current												
		200A	400A	450A	600A	800A	900A	1000A	1200A	1350A	1500A	1600A	1800A	2400A
	1700V					•			-					
Rated voltage	3300V					-		_					•	
veiluge	4500V			•					_					
	6500V													



X Series HVIGBT Modules std type



Existing compatible package: standard type contributes to smaller, higher-capacity inverter systems by expanding lineup

- <Main Features>
- ${}^{\raisebox{3.5pt}{\text{\circle*{1.5}}}} Power loss reduced by incorporating 7th-generation IGBT and RFC <math display="inline">{}^{\raisebox{3.5pt}{\text{\circle*{1.5}}}}$ diode
- *Compared to the existing CM900HC-90H and CM1350HC-90X, the new models' rated output currents are 50% greater but external dimensions are the same.
- Compared to existing CM900HC-90H, new CM900HC-90X, etc. are 33% smaller but achieve the same voltage and current ratings.
- Optimal package internal structure realizes improved heat dissipation, humidity resistance and flame retardance, increasing product life

Product lineup

std type	1.7kV	3.3kV	4.5kV	6.5kV
	2400A	1200A	900A 1000A	600A
	2400A	1200A 1800A	900A 1350A 1500A	600A 900A 1000A

X Series HVIGBT Modules dual type

New common frame package: dual type class-leading current density contributes to increased power output in inverter systems

<Main Features>

- Power loss reduced by incorporating 7th-generation IGBT and RFC *1 diode
- Industry's highest 3.3kV/600A Si module power density of 8.57A/cm^{2 *2} contributes to increased power output and efficiency
- •Terminal layout optimized for easy paralleling and flexible inverter configurations and capacities
- •New package structure offers extra reliability
 - *2 As of Dec. 17, 2020 based on Mitsubishi Electric research

Product lineup



HV100	3.3kV	4.5kV
	450A 600A	450A

^{*1} RFC : Relaxed field of cathode

Series Matrix of HVIGBT(No.: Number of Outline Drawing, see page 35)

Vces					1700	1700V							3300V											
10	X-Ser	ies			S-Seri N-Ser	ies			H-Ser	ies			X-Ser	ies			R-Ser	ies			H-Ser	ies		
lc	Conne	ction	Туре	No.	Connec		Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.
400A																					CM400HG-66H CM400DY-66H	H D1		- 06
450A													CM450DA-66X CM450DE-66X	D2 D2	A E	07 08								
600A									CM600DY-34H CM600E2Y-34H	D1 E2	B2 B2	01 01	CM600DA-66X CM600DE-66X CM600E1A-66X*	D2 D2 E1	A E A	07 08 07								
800A					CM800DZB-34N	D1	C2	-	CM800DZ-34H	D1	C2	-									CM800HC-66H CM800E4C-66H CM800E6C-66H	H E4 E2	C1 C1 C1	-
1000A																	CM1000HC-66R CM1000E4C-66R		C1 C1	-				
1200A	CM1200DA-34X	D2	Α	07	CM1200HCB-34N CM1200DC-34N CM1200E4C-34N CM1200DC-34S CMH1200DC-34S	H D1 E4 D1 D1	C2 C2 C2 C2 C2	- - - - 01	CM1200HC-34H	Н	C2	-	CM1200HC-66X CM1200HCB-66X	H H	C1 C1	02 03					CM1200HG-66H CM1200HC-66H	H	C1 C1	-
1500A																	CM1500HC-66R	Н	C1	-				
1600A									CM1600HC-34H	Н	C2	-												
1800A					CM1800HC-34N CM1800HCB-34N	H	C2 C2	-	CM1800HC-34H	Н	C2	-	CM1800HC-66X CM1800HG-66X	H	C1 G	03 04								
2400A	CM2400HC-34X CM2400HCB-34X	Н	C1 C1	02 03	CM2400HC-34N CM2400HCB-34N	H	C2 C2	-	CM2400HC-34H	Н	C2	03												
Connection	H			E1		I	≣2/	E6		E	4		: : : : : : : : : : : : : : : : : : :	D1	1 1 1 1	一大工工工	D2							

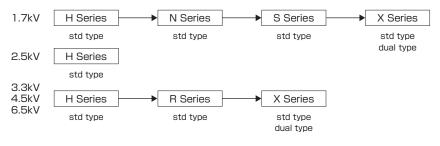
[Type]
A:Al base plate 6kV Isolation
B1:Cu base plate / 6kV Isolation
B2:Cu base plate / 4kV Isolation

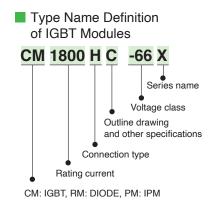
E:Al base plate 10kV Isolation

C1:AISiC base plate / 6kV Isolation C2:AISiC base plate / 4kV Isolation G:AISiC base plate 10kV Isolation The outline drawing is written the figure of principal part numbers that have a common dimension.

Non-recommended: Please contact to the sales offices.

Evolution of HVIGBT Module Series





★: New Product

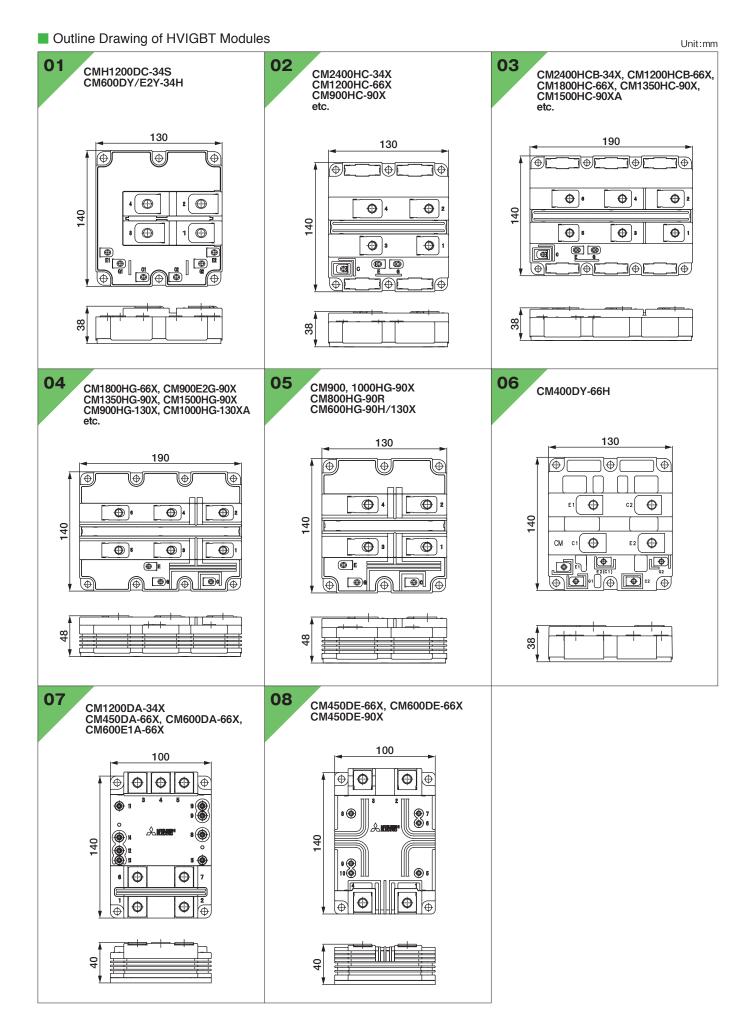
Series Matrix of HVIGBT(No.: Number of Outline Drawing, see page 35)

Vces					4500V											650	OOV			
Ic	X-Series	3			R-Series	3			H-Series	3			X-Series	;			H-Series	3		
.0	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Conne	ction	Туре	No.	Connec	ction	Туре	No.	Connec	ction	Туре	No.
200A																	CM200HG-130H	Н	G	-
400A																	CM400HG-130H CM400E2G-130H CM400E4G-130H	H E2 E4	G G G	-
450A	CM450DE-90X**	D2	E	08																
600A									CM600HG-90H	Н	G	05	CM600HG-130X	Н	G	05	CM600HG-130H	Н	G	-
800A					CM800HC-90R CM800HG-90R	Н	C1 G	02 05												
900A	CM900HC-90X CM900HG-90X CM900E2G-90X	Н	G	02 05 04					CM900HC-90H CM900HG-90H	H	C1 G	-	CM900HG-130X	Н	G	04				
1000A	CM1000HG-90X	Н	G	05									CM1000HG-130XA	Н	G	04				
1200A					CM1200HC-90RA CM1200HG-90R	Н	C1 G	-												
1350A	CM1350HC-90X CM1350HG-90X	Н	C1 G	03 04																
1500A	CM1500HC-90XA CM1500HG-90X			03 04																
Connection	Н	E	2		— E4 —	£	0		D2											

[Type]
A:Al base plate 6kV Isolation
B1:Cu base plate / 6kV Isolation
B2:Cu base plate / 4kV Isolation
C1:AlSiC base plate / 6kV Isolation
C2:AlSiC base plate / 4kV Isolation
C3:AlSiC base plate / 4kV Isolation
E:Al base plate 10kV Isolation
E:Al base plate 10kV Isolation

★★: Under Development
The outline drawing is written the figure of principal part numbers that have a common dimension.

Non-recommended: Please contact to the sales offices.



HVDIODE Modules

Series, Main Application

Series	Main Application
HVDIODE Modules	Traction/Power transmission/Motion control

Data sheet here



Rated Lineup

						Rated	current					
		300A	400A	450A	600A	750A	800A	900A	1000A	1200A	1500A	1800A
	1700V									•		•
Rated	3300V		•		-					•		
voltage	4500V			•			•					
	6500V	•							-			

Series Matrix of HVDIODE Modules (No.: Number of outline drawing, see page 37)

VPRM	1700V	Connecti	ion ITv	nol N	3300V	Connection	n lTvr	nel No	4500V	Connec	tion	Tyne	al No	6500V	Connection	ın İTi	vna I	Vo.
300A		Connect	ion i y	po IV	0.	Toolinection	1 7 7 5	140.		Connec	MIOII	урс	INU.	RM300DG-130X*			G O	
400A					RM400DG-66S RM400DY-66S	D		-									I	_
450A									RM450DG-90X		D	G	09	RM450DG-130X*	[) (G C)9
600A					RM600DY-66S RM600DC-66X	D		10						RM600DG-130S RM600DG-130X*		0 (G C	19 19
750A									RM750DC-90X**		D	С	10				\top	_
800A									RM800DG-90F		D	G	09				T	_
900A									RM900HC-90S RM900DB-90S RM900DG-90X*		H D D	В	- 10 09					
1000A					RM1000DC-66F	D	С	; -						RM1000DG-130XA	[) (G C	19
1200A	RM1200DB-34S	1	D E	3 -	RM1200DG-66S RM1200HE-66S RM1200DB-66S RM1200DC-66X* RM1200DG-66X	D H D D	B	; -	RM1200DG-90F		D	G	09					_
1500A					RM1500HE-66F RM1500DC-66F	H			RM1500DG-90X*		D	G	09				I	_
1800A	RM1800HE-34S		H C) .													\perp	_
Connection	H D F																	

[Type]

B:Cu base plate 6kV Isolation

C:AISiC base plate 6kV Isolation

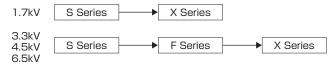
G:AISiC base plate 10kV Isolation

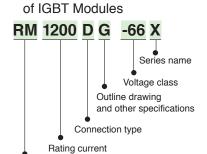
★: New Product ★★: Under Development The outline drawing is written the figure of principal part numbers that have a common dimension.

Non-recommended: Please contact to the sales offices.

Type Name Definition

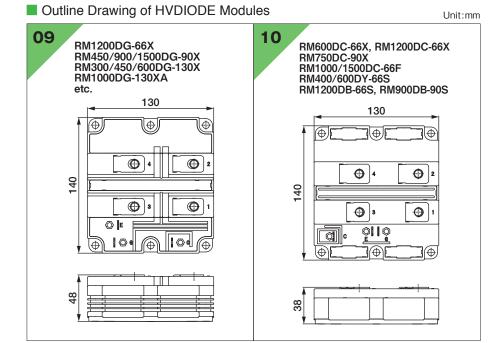
Evolution of HVDIODE Module Series





CM: IGBT, RM: DIODE, PM: IPM

Lineup of HVDIODE Modules



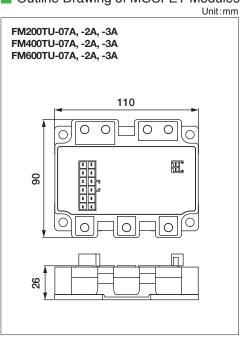
Lineup of MOSFET Modules

Series Matrix of MOSFET Modules

RoHS directive (2011/65/EU, (EU)2015/863) compliant

VDSS	75V		100V		150V	
ID \	/50	Connection	1000	Connection	1500	Connection
100A	FM200TU-07A	T	FM200TU-2A	Т	FM200TU-3A	Т
200A	FM400TU-07A	Т	FM400TU-2A	Т	FM400TU-3A	Т
300A	FM600TU-07A	Т	FM600TU-2A	Т	FM600TU-3A	Т
Connection						

Outline Drawing of MOSFET Modules



Data sheet here



Power Modules for xEV

Series, Main Application

	Series	Main Application
J1	-	xEV

Rated Lineup

		Rated (current
		600A	700A
Rated voltage	650V		



Featured Products

Package with 6-in-1 connection and integrated water-cooled fin contributes to more compact, high-power

J1 Series power Modules for xEV

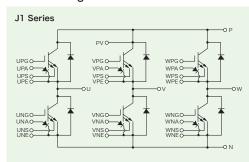
CT600C1A060-A, CT700CJ1A060-A

- <Main Features>
- •Integrated direct water-cooling structure with cooling fins and 6-in-1 connection contribute to more compact inverters for xEV
- $\bullet \text{Direct lead bonding (DLB) structure ensures high reliability} \\$
- -Loss further reduced by incorporating 7th-generation IGBT built with a $\mathsf{CSTBT}^\mathsf{TM*}$ structure
- •On-chip current sensor that enables high-speed current-cutoff protection is installed
- •Completely lead-free, confirms to RoHS directive (2011/65/EU)
- •Suitable for a variety of electric and hybrid vehicle inverters

*CSTBT: Mitsubishi Electric's unique IGBT that utillizes the carrier cumulative effect.



Block Diagram



Features

Common

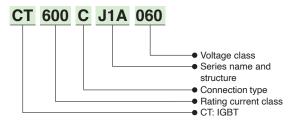
- Long power/temperature cycle life
- High-precision on-chip temperrature sensor
- High traceability in managing materials/components for each product throughout the entire production process
- Package structure compliant with the End-of-Life-Vehicles Directive, regulations relating to substances of environmental concern

Power Modules for xEV

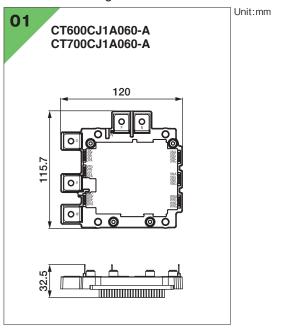
■ Matrix of 650V Power Modules

Vces	650V		
Series	J1 Series		
lc	Power Module with pin fin	Connection	No.
300A	_	_	_
600A	CT600CJ1A060-A	С	01
700A	CT700CJ1A060-A	С	01
Connection	C		

■ Type Name Definition of Power Modules for xEV



Outline Drawing of Power Modules for xEV



MEMO

MEMO

Mitsubishi Electric Semiconductors & Devices Website

www.MitsubishiElectric.com/semiconductors/



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